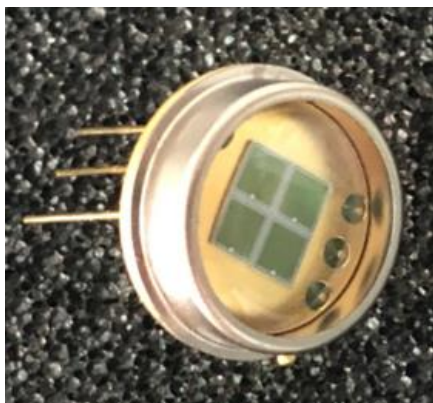


SILICON UV QUADRANT PHOTODIODE



Description

4*3*3mm² active area, low dark current
 UV enhanced quadrant photodiode with P on N
 Construction .

Features

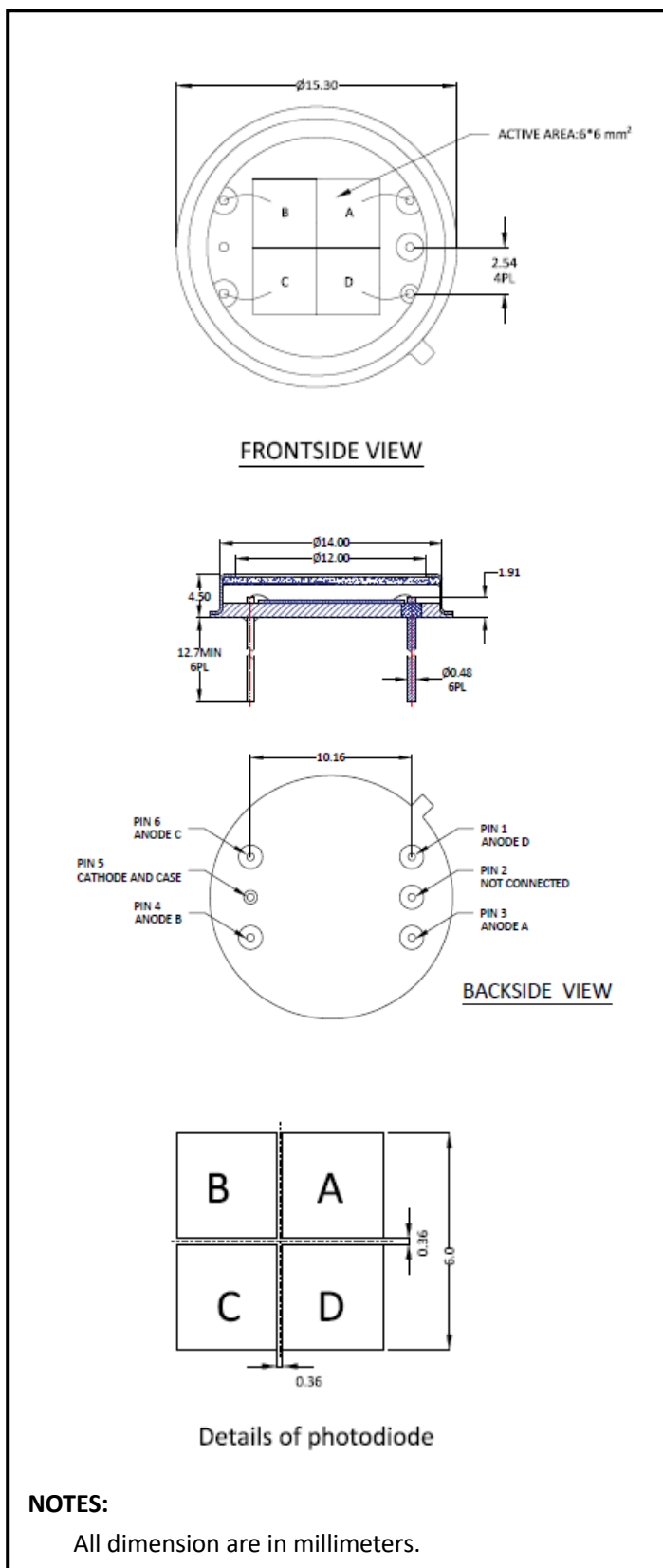
- * Small gap (36um)
- * Low dark current
- * High resolution
- * Operating temperature is from -40 to +80°C
- * Storage temperature is from -40 to +100°C
- * soldering temperature is 260°C @Max.5 seconds
 at the position of 2mm from the PIN legs.

General Ratings

- * Type Silicon Photodiode
- * High linearity * Low dark current

Applications

- * Laser beam position sensor * Autocollimators
- * Optical tweezers * Ellipsometers





Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Number of elements			4			
Active area			6.0*6.0			mm
Gap		Between elements	36			um
Spectral range			190		1100	nm
Photo sensitivity	S _R	360nm		0.1		A/W
		635nm		0.38		
Dark current	I _D	V _R =10mV		0.13		nA
		V _R =10V		0.39	2	
Rise time	t _R	V _R =10V; λ =375m;R _L =50Ω		50		ns
Tempcoeffi-cient of I _D	T _{CID}			0.18		times/°C
Operating voltage	V _{OP}		0		50	V
Reverse breakdown voltage	V _{(BR)R}	I _R =100μA Ev=0lx	33			V
Junction Capacitance	C _J	V _R =0V f=1MHz		307		pF
		V _R =10V f=1MHz		12		
CrossTalk Channel-to-Channel		400-850nm, Adjacent Channel		0.1	0.5	%
		850-1100nm, Adjacent Channels		1	5	
Uniformity of each Element	%		0.8		2	%
Shunt resistance	R _{sh}	V _R =10mV		0.077		GΩ
Rsh Temperature Coefficient	TC Rsh			0.18		%/°C
Angular Resp 50% Resp Pt	ε _{1/2}			±60		Degrees
Noise Equivalent Power	NEP	V _R =10V λ =940nm		4×10 ⁻¹⁴		W/Hz ^{1/2}
Specific Detectivity	D*	V _R =10V λ =940nm		3.43×10 ¹³		cm(Hz/W) ^{1/2}

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject change without notice

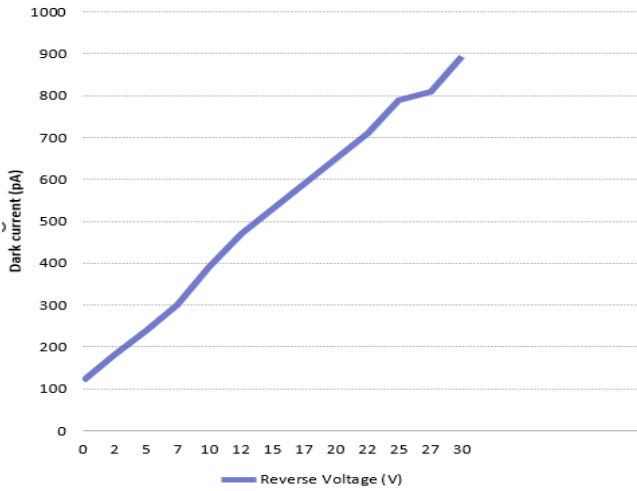
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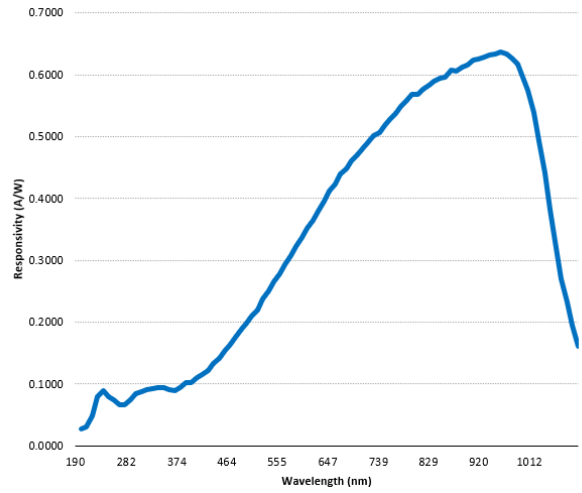
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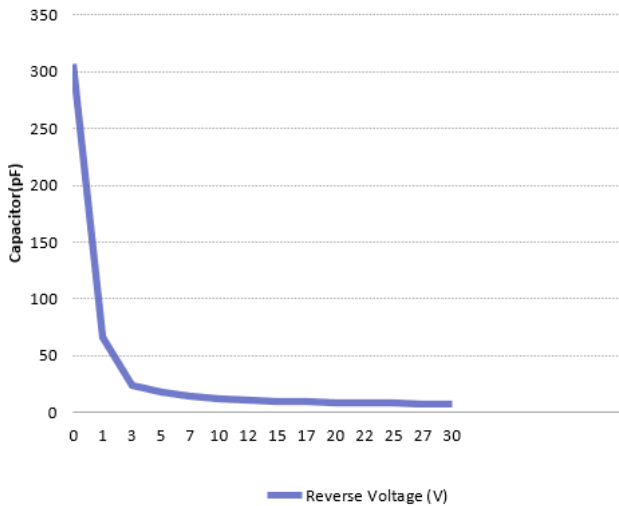
■ Dark current vs. reverse voltage



■ Spectral response



■ Relative Junction Capacitance VS. Voltage



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